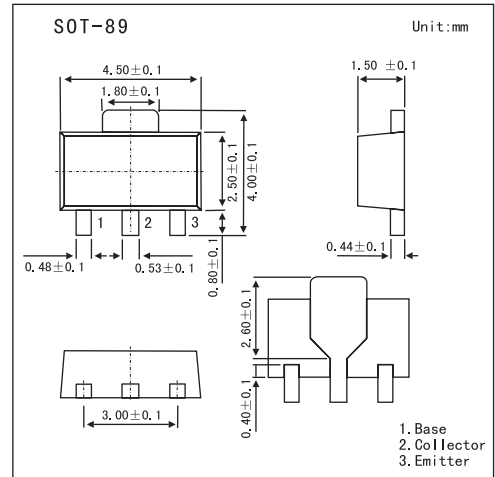


■ Features

- Large current capacity.
- Low collector-to-emitter saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	15	V
Collector-emitter voltage	V _{CE0}	15	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	1.5	A
Collector current (pulse)	I _{CP}	3	A
Base current	I _B	300	mA
Collector dissipation, mounted on ceramic board(250mm ² X0.8mm)	P _C	1.3	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	ICBO	V _{CB} = 12 V, I _E =0			100	nA
Emitter cutoff current	IEBO	V _{EB} = 4 V, I _C =0			100	nA
DC current gain	hFE	V _{CE} = 2V, I _C = 50mA	140		560	
Gain bandwidth product	f _T	V _{CE} = 2V, I _C = 50mA		200		MHz
Output capacitance	C _{ob}	V _{CB} = 10V, f = 1.0MHz		10		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 5 mA, I _B = 0.5 mA		10	25	mV
		I _C = 500 mA, I _B = 25 mA		120	240	
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 500 mA, I _B = 25 mA		0.9	1.2	mV
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	15			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	15			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5			V

■ hFE Classification

Marking	CT		
	S	T	U
hFE	140~280	200~400	280~560